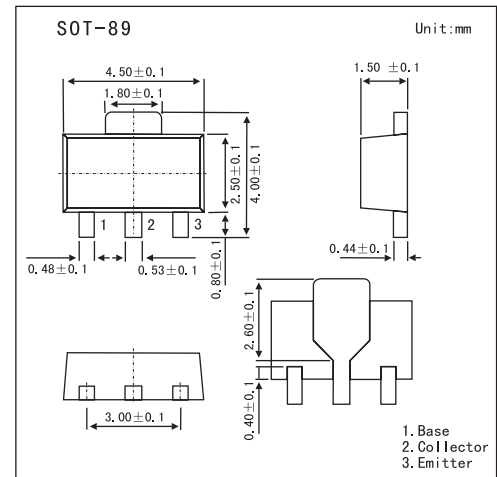


## Low Frequency Transistor

## 2SB1386

## ■ Features

- Low  $V_{CE(sat)}$ .  
 $V_{CE(sat)} = -0.35V$  (Typ.)  
( $I_C/I_B = -4A / -0.1A$ )
- Excellent DC current gain
- Epitaxial planar type
- PNP silicon transistor

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-30	V
Collector-emitter voltage	$V_{CE0}$	-20	V
Emitter-base voltage	$V_{EB0}$	-6	V
Collector current	$I_C$	-5	A
Collector current(Pulse)	$I_{CP}^*$	-10	A
Collector power dissipation	$P_C$	0.5	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\* Single pulse,  $P_w=10ms$

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$BV_{CB0}$	$I_C = -50\mu A$	-30			V
Collector-emitter breakdown voltage	$BV_{CE0}$	$I_C = -1mA$	-20			V
Emitter-base breakdown voltage	$BV_{EB0}$	$I_E = -50\mu A$	-6			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20V$			-0.5	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5V$			-0.5	$\mu A$
DC current transfer ratio	$V_{CE(sat)}$	$I_C = -4A, I_B = -0.1A$			-1	V
Collector-emitter saturation voltage	$h_{FE}$	$V_{CE} = -2V, I_C = -0.5A$	82		390	
Transition frequency	$C_{ob}$	$V_{CE} = -6V, I_E = 50mA, f = 30MHz$		120		MHz
Output capacitance	$f_r$	$V_{CB} = -20V, I_E = 0A, f = 1MHz$		60		pF

■  $h_{FE}$  Classification

Marking	BH		
	P	Q	R
$h_{FE}$	82~180	120~270	180~390